# UNISONIC TECHNOLOGIES CO., LTD

13005EC

**Preliminary** 

### NPN SILICON TRANSISTOR

## NPN SILICON POWER TRANSISTORS

#### DESCRIPTION

These devices are designed for high-voltage, high-speed power switching inductive circuits where fall time is critical. They are particularly suited for 115 and 220 V SWITCHMODE.

#### **■ FEATURES**

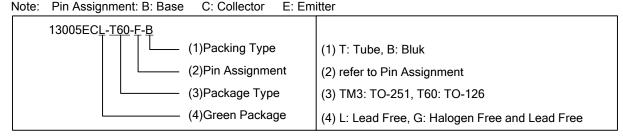
- \*  $V_{CES} = 850 \text{ V}$
- \* Reverse bias SOA with inductive loads @ T<sub>C</sub> = 100°C
- \* Inductive switching matrix 2 to 4 Amp, 25 and 100°C t<sub>C</sub> @ 3A, 100°C is 180 ns (Typ)
- \* 850V blocking capability
- \* SOA and switching applications information

#### ■ APPLICATIONS

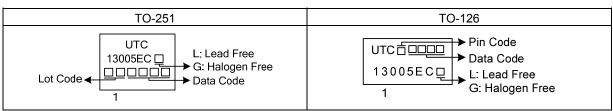
- \* Switching regulator's, inverters
- \* Motor controls
- \* Solenoid/Relay drivers
- \* Deflection circuits

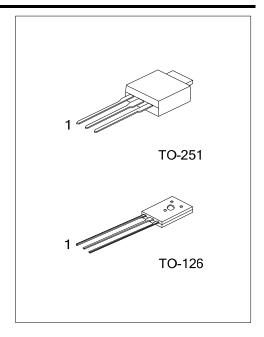
## ■ ORDERING INFORMATION

	Ordering	Dookogo	Pin Assignment			Dooking		
	Lead Free	Halogen Free	Package	1	2	3	Packing	
	13005ECL-x-TM3-T	13005ECG-x-TM3-T	TO-251	В	С	E	Tube	
	13005ECL-x-T60-F-K 13005ECG-x-T60-F-K		TO-126	В	O	E	Bulk	
١	Note: Pin Assignment: B: Base					_		



## MARKING INFORMATION





www.unisonic.com.tw 1 of 4

#### ■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage		V <sub>CEO(SUS)</sub>	400	V
Collector-Emitter Voltage (V <sub>BE</sub> =0)		V <sub>CES</sub>	850	V
Collector-Base Voltage		$V_{CBO}$	850	V
Emitter Base Voltage		$V_{EBO}$	9	V
0-11	Continuous	I <sub>C</sub>	4	Α
Collector Current	Peak (1)	I <sub>CM</sub>	8	Α
Dana Command	Continuous	I <sub>B</sub>	2	Α
Base Current	Peak (1)	I <sub>BM</sub>	4	Α
F:# O	Continuous	Ι <sub>Ε</sub>	6	Α
Emitter Current	Peak (1)	I <sub>EM</sub>	12	Α
Danier Diagination at T. 05°C	TO-251	-	10	W
Power Dissipation at T <sub>C</sub> =25°C	TO-126	P <sub>D</sub>	8	W
Junction Temperature		TJ	-65 ~ +150	°C
Storage Temperature Range		T <sub>STG</sub>	-65 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

#### **■ THERMAL DATA**

PARAMETER		SYMBOL	RATINGS	UNIT	
lunation to Ambient	TO-251	95		°C/\\/	
Junction to Ambient	TO-126	$\theta_{JA}$	100	°C/W	
lunation to Coop	TO-251	0	13	2004	
Junction to Case	TO-126	$\theta_{ m JC}$	16.25	°C/W	

### ■ **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub>=25°C, unless otherwise specified)

PARAMETER SYI		TEST CONDITIONS MIN		TYP	MAX	UNIT
OFF CHARACTERISTICS (Note 1)				_		
Collector-Emitter Voltage	V <sub>CES</sub>	I <sub>C</sub> =10mA , V <sub>BE</sub> =0	850			V
		V <sub>CBO</sub> =Rated Value, V <sub>BE(OFF)</sub> =1.5V			1	
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CBO</sub> =Rated Value,			5	mA
		V <sub>BE(OFF)</sub> =1.5V, T <sub>C</sub> =100°C				
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =9V, I <sub>C</sub> =0			1	mA
ON CHARACTERISTICS (Note 1)						
	h <sub>FE1</sub>	I <sub>C</sub> =0.5A, V <sub>CE</sub> =5V	15		50	
DC Current Gain	h <sub>FE2</sub>	I <sub>C</sub> =1A, V <sub>CE</sub> =5V	10		60	
	h <sub>FE3</sub>	I <sub>C</sub> =2A, V <sub>CE</sub> =5V	8		40	
		I <sub>C</sub> =1A, I <sub>B</sub> =0.2A			0.5	V
Callegtor Emitter Seturation Voltage	\ \/	I <sub>C</sub> =2A, I <sub>B</sub> =0.5A			0.6	V mA mA V V V V V V V V V V V V P MHz pF
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	I <sub>C</sub> =4A, I <sub>B</sub> =1A			1	V
		I <sub>C</sub> =2A, I <sub>B</sub> =0.5A, T <sub>A</sub> =100°C			1	V
	V <sub>BE(SAT)</sub>	I <sub>C</sub> =1A, I <sub>B</sub> =0.2A			1.2	V
Base-Emitter Saturation Voltage		I <sub>C</sub> =2A, I <sub>B</sub> =0.5A			1.6	V
		I <sub>C</sub> =2A, I <sub>B</sub> =0.5A, T <sub>C</sub> =100°C			1.5	V
DYNAMIC CHARACTERISTICS						
Current-Gain-Bandwidth Product	$f_T$	I <sub>C</sub> =500mA, V <sub>CE</sub> =10V, f=1MHz	4			MHz
Output Capacitance	C <sub>OB</sub>	$V_{CB}$ =10V, $I_E$ =0, f=0.1MHz		65		pF
SWITCHING CHARACTERISTICS						
Resistive Load (Table 1)						
Delay Time	t <sub>D</sub>			0.025	0.1	μs
Rise Time	$t_R$ $V_{CC}$ =12			0.3	0.7	μs
Storage Time	ts	t <sub>P</sub> =25µs, Duty Cycle≤1%		1.7	4	μs
Fall Time	t <sub>F</sub>	0.4 0		0.9	μs	

Note: 1. Pulse Test: Pulse Width=5ms, Duty Cycle≤10%

## ■ CLASSIFICATION OF h<sub>FE1</sub>

RANK	Α	В	С	D	E
RANGE	15 ~ 20	20 ~ 25	25 ~ 30	30 ~ 40	40 ~ 50

<sup>2.</sup> Pulse Test: P<sub>W</sub>=300µs, Duty Cycle≤2%

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